2SC4262

Silicon NPN Epitaxial

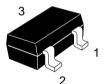
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Application

UHF / VHF Local oscillator

Outline

CMPAK



- 1. Emitter
- 2. Base
- 3. Collector



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Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

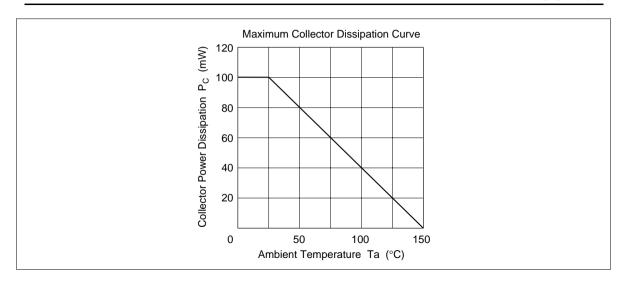
Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	20	V	
Collector to emitter voltage	V_{CEO}	15	V	
Emitter to base voltage	V_{EBO}	3	V	
Collector current	I _c	50	mA	
Collector power dissipation	P _c	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Electrical Characteristics (Ta = 25°C)

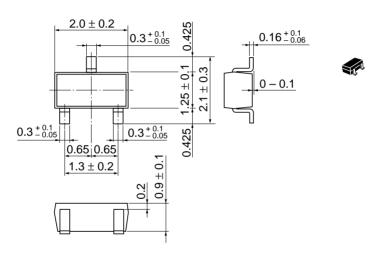
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\text{(BR)CBO}}$	20	_	_	V	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{\text{(BR)CEO}}$	15	_	_	V	I_{C} = 1 mA, R_{BE} = ∞
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 15 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	1.0	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
Collector to emitter saturation voltage	$\boldsymbol{V}_{\text{CE(sat)}}$	_	_	0.5	V	$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 4 mA
DC current transfer ratio	h _{FE}	50	_	200		$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$
Collector output capacitance	Cob	_	_	1.0	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{MHz}$
Gain bandwidth product	$f_{\scriptscriptstyle T}$	1.4	2.9	_	GHz	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$

Note: Marking is "IP-".

See characteristic curves of 2SC3793.



Unit: mm



Hitachi Code	CMPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.006 g

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